

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
21 April 2005 (21.04.2005)

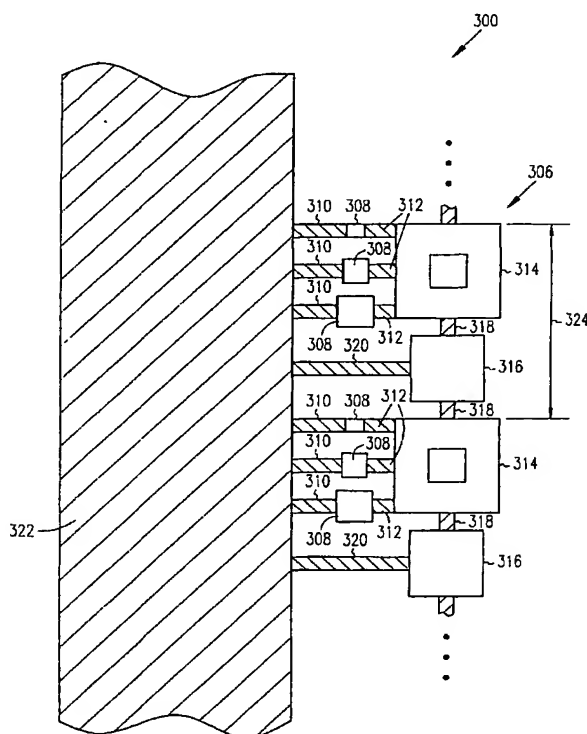
PCT

(10) International Publication Number
WO 2005/036737 A1

- (51) International Patent Classification⁷: **H03F 3/60**, 1/02, 1/52
- (21) International Application Number: **PCT/US2004/026051**
- (22) International Filing Date: 11 August 2004 (11.08.2004)
- (25) Filing Language: English
- (26) Publication Language: English
- (30) Priority Data:
10/664,112 17 September 2003 (17.09.2003) US
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- (81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.
- (84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI,

[Continued on next page]

(54) Title: **MONOLITHIC ARRAY AMPLIFIER WITH PERIODIC BIAS-LINE BYPASSING STRUCTURE AND METHOD**



(57) Abstract: A bias-line bypassing structure (300) comprises a plurality of bias-line bypass circuits (306) forming a periodic structure at least partially around each of a plurality of amplification units (302) to reduce RF current flow between the amplification units and a grid-bias network (304). Each bias-line bypass circuit (306) may comprise thin-film capacitors (308), inductive wire bridges (310), and thin-film resistors (312) connected to ground vias (314). The thin-film capacitors (308) may have differing values selected to resonate with an associated one of the inductive wire bridges (310) and an associated one of the thin-film resistors (312) to shunt RF current flow over a range of RF frequencies. In some embodiments, the inductive wire bridges (310) may comprise inductive wire-bridge fuses to provide an open circuit in case an associated one of the thin-film capacitors (308) shorts to ground.

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SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ,
GW, ML, MR, NE, SN, TD, TG).

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Published:

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